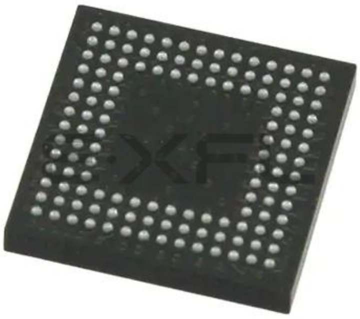
Lattice Semiconductor Corporation - LCMXO2-256HC-6MG132C Datasheet



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Understanding Embedded - FPGAs (Field Programmable Gate Array)

Embedded - FPGAs, or Field Programmable Gate Arrays, are advanced integrated circuits that offer unparalleled flexibility and performance for digital systems. Unlike traditional fixed-function logic devices, FPGAs can be programmed and reprogrammed to execute a wide array of logical operations, enabling customized functionality tailored to specific applications. This reprogrammability allows developers to iterate designs quickly and implement complex functions without the need for custom hardware.

Applications of Embedded - FPGAs

The versatility of Embedded - FPGAs makes them indispensable in numerous fields. In telecommunications,

Details	
Product Status	Active
Number of LABs/CLBs	32
Number of Logic Elements/Cells	256
Total RAM Bits	-
Number of I/O	55
Number of Gates	-
Voltage - Supply	2.375V ~ 3.465V
Mounting Type	Surface Mount
Operating Temperature	0°C ~ 85°C (TJ)
Package / Case	132-LFBGA, CSPBGA
Supplier Device Package	132-CSPBGA (8x8)
Purchase URL	https://www.e-xfl.com/product-detail/lattice-semiconductor/lcmxo2-256hc-6mg132c

Table 2-5. sysMEM Block Configurations

Memory Mode	Configurations
Single Port	8,192 x 1 4,096 x 2 2,048 x 4 1,024 x 9
True Dual Port	8,192 x 1 4,096 x 2 2,048 x 4 1,024 x 9
Pseudo Dual Port	8,192 x 1 4,096 x 2 2,048 x 4 1,024 x 9 512 x 18
FIFO	8,192 x 1 4,096 x 2 2,048 x 4 1,024 x 9 512 x 18

Bus Size Matching

All of the multi-port memory modes support different widths on each of the ports. The RAM bits are mapped LSB word 0 to MSB word 0, LSB word 1 to MSB word 1, and so on. Although the word size and number of words for each port varies, this mapping scheme applies to each port.

RAM Initialization and ROM Operation

If desired, the contents of the RAM can be pre-loaded during device configuration. EBR initialization data can be loaded from the UFM. To maximize the number of UFM bits, initialize the EBRs used in your design to an all-zero pattern. Initializing to an all-zero pattern does not use up UFM bits. MachXO2 devices have been designed such that multiple EBRs share the same initialization memory space if they are initialized to the same pattern.

By preloading the RAM block during the chip configuration cycle and disabling the write controls, the sysMEM block can also be utilized as a ROM.

Memory Cascading

Larger and deeper blocks of RAM can be created using EBR sysMEM Blocks. Typically, the Lattice design tools cascade memory transparently, based on specific design inputs.

Single, Dual, Pseudo-Dual Port and FIFO Modes

Figure 2-8 shows the five basic memory configurations and their input/output names. In all the sysMEM RAM modes, the input data and addresses for the ports are registered at the input of the memory array. The output data of the memory is optionally registered at the memory array output.

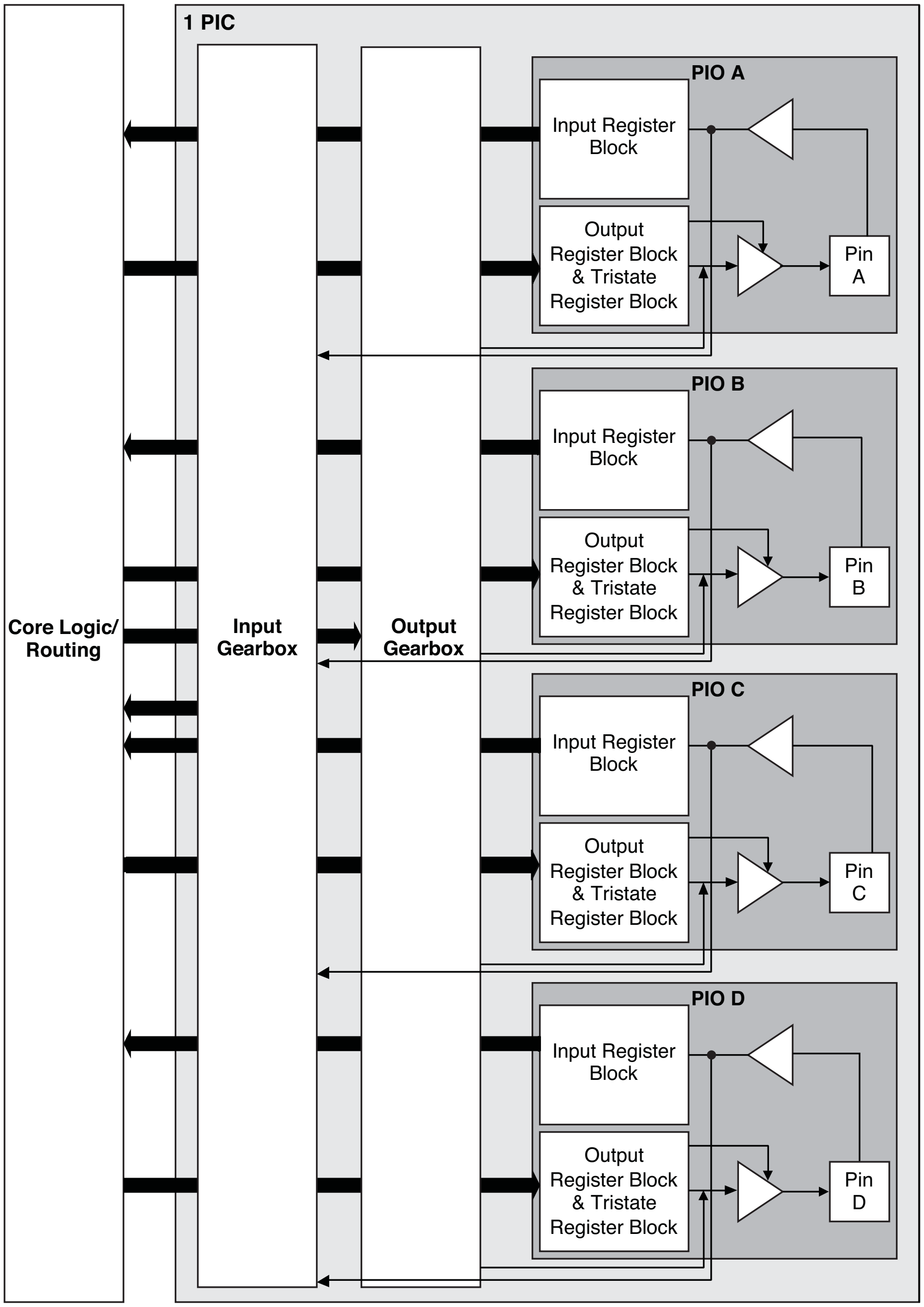
Programmable I/O Cells (PIC)

The programmable logic associated with an I/O is called a PIO. The individual PIO are connected to their respective sysIO buffers and pads. On the MachXO2 devices, the PIO cells are assembled into groups of four PIO cells called a Programmable I/O Cell or PIC. The PICs are placed on all four sides of the device.

On all the MachXO2 devices, two adjacent PIOs can be combined to provide a complementary output driver pair.

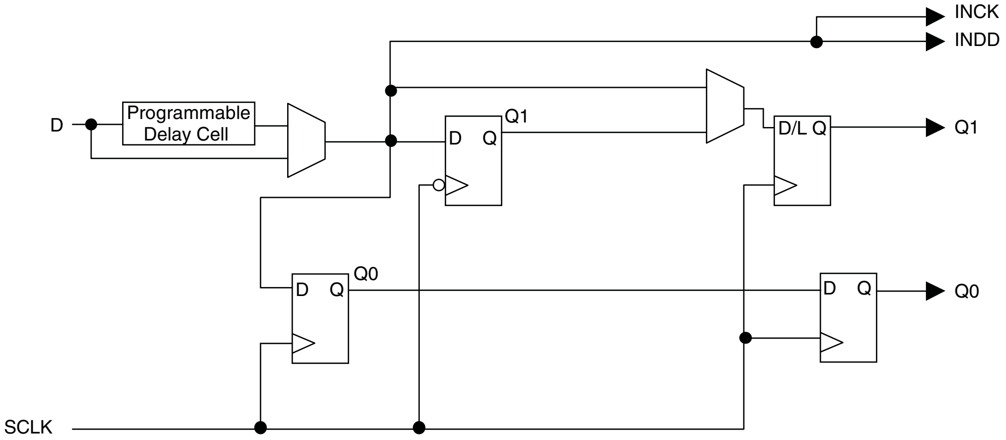
The MachXO2-640U, MachXO2-1200/U and higher density devices contain enhanced I/O capability. All PIO pairs on these larger devices can implement differential receivers. Half of the PIO pairs on the top edge of these devices can be configured as true LVDS transmit pairs. The PIO pairs on the bottom edge of these higher density devices have on-chip differential termination and also provide PCI support.

Figure 2-11. Group of Four Programmable I/O Cells



Notes:
1. Input gearbox is available only in PIC on the bottom edge of MachXO2-640U, MachXO2-1200/U and larger devices.
2. Output gearbox is available only in PIC on the top edge of MachXO2-640U, MachXO2-1200/U and larger devices.

Figure 2-12. MachXO2 Input Register Block Diagram (PIO on Left, Top and Bottom Edges)



Right Edge

The input register block on the right edge is a superset of the same block on the top, bottom, and left edges. In addition to the modes described above, the input register block on the right edge also supports DDR memory mode.

In DDR memory mode, two registers are used to sample the data on the positive and negative edges of the modified DQS (DQSR90) in the DDR Memory mode creating two data streams. Before entering the core, these two data streams are synchronized to the system clock to generate two data streams.

The signal DDRCLKPOL controls the polarity of the clock used in the synchronization registers. It ensures adequate timing when data is transferred to the system clock domain from the DQS domain. The DQSR90 and DDRCLKPOL signals are generated in the DQS read-write block.

Figure 2-13. MachXO2 Input Register Block Diagram (PIO on Right Edge)

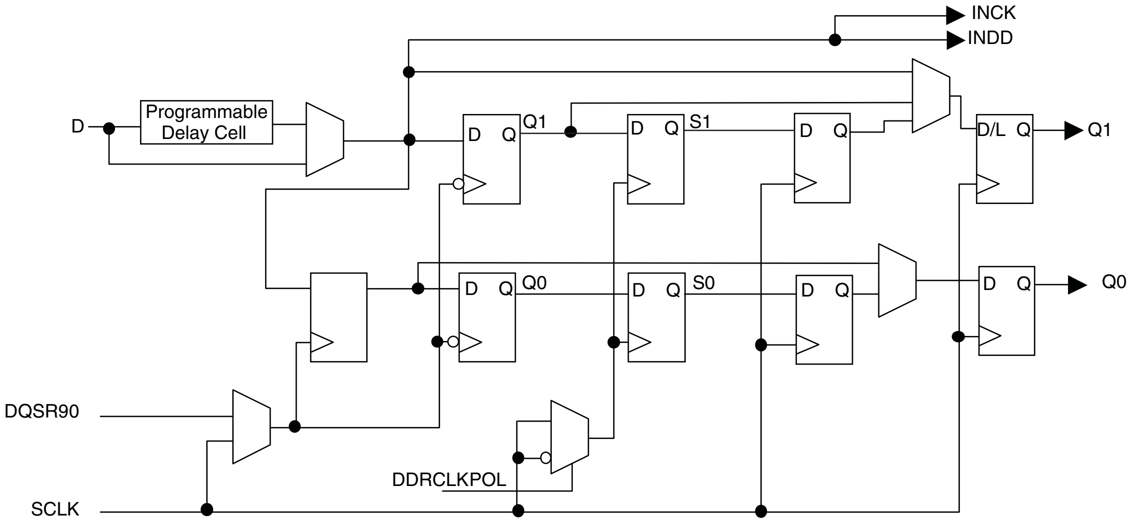


Figure 2-18. MachXO2-1200U, MachXO2-2000/U, MachXO2-4000 and MachXO2-7000 Banks

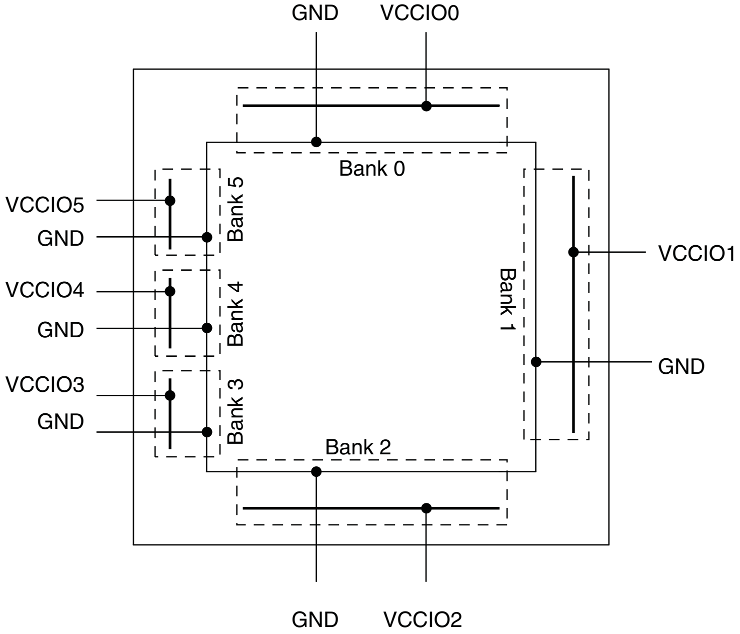
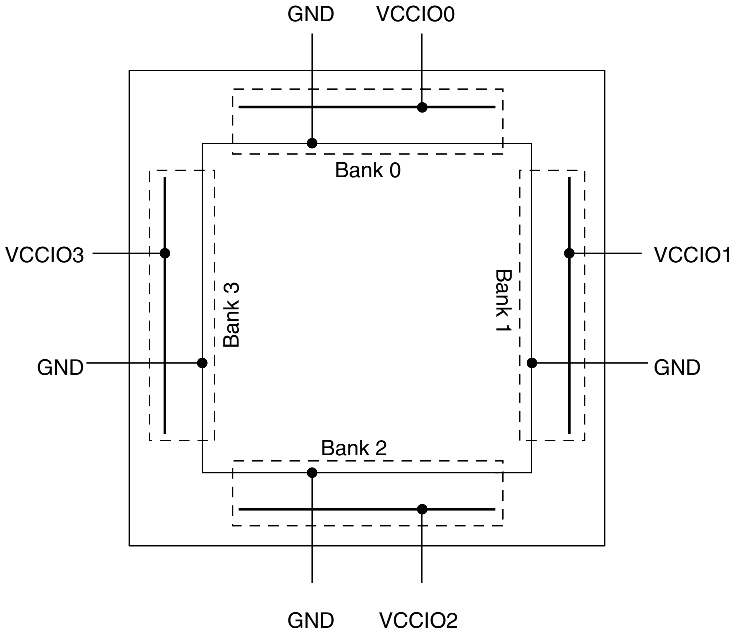


Figure 2-19. MachXO2-256, MachXO2-640/U and MachXO2-1200 Banks



For more details on these embedded functions, please refer to TN1205, Using User Flash Memory and Hardened Control Functions in MachXO2 Devices.

User Flash Memory (UFM)

MachXO2-640/U and higher density devices provide a User Flash Memory block, which can be used for a variety of applications including storing a portion of the configuration image, initializing EBRs, to store PROM data or, as a general purpose user Flash memory. The UFM block connects to the device core through the embedded function block WISHBONE interface. Users can also access the UFM block through the JTAG, I^2C and SPI interfaces of the device. The UFM block offers the following features:

- Non-volatile storage up to 256 kbits
- 100K write cycles
- Write access is performed page-wise; each page has 128 bits (16 bytes)
- Auto-increment addressing
- WISHBONE interface

For more information on the UFM, please refer to TN1205, Using User Flash Memory and Hardened Control Functions in MachXO2 Devices.

Standby Mode and Power Saving Options

MachXO2 devices are available in three options for maximum flexibility: ZE, HC and HE devices. The ZE devices have ultra low static and dynamic power consumption. These devices use a 1.2 V core voltage that further reduces power consumption. The HC and HE devices are designed to provide high performance. The HC devices have a built-in voltage regulator to allow for 2.5 V V_{CC} and 3.3 V V_{CC} while the HE devices operate at 1.2 V V_{CC}.

MachXO2 devices have been designed with features that allow users to meet the static and dynamic power requirements of their applications by controlling various device subsystems such as the bandgap, power-on-reset circuitry, I/O bank controllers, power guard, on-chip oscillator, PLLs, etc. In order to maximize power savings, MachXO2 devices support an ultra low power Stand-by mode. While most of these features are available in all three device types, these features are mainly intended for use with MachXO2 ZE devices to manage power consumption.

In the stand-by mode the MachXO2 devices are powered on and configured. Internal logic, I/Os and memories are switched on and remain operational, as the user logic waits for an external input. The device enters this mode when the standby input of the standby controller is toggled or when an appropriate I^2C or JTAG instruction is issued by an external master. Various subsystems in the device such as the band gap, power-on-reset circuitry etc can be configured such that they are automatically turned “off” or go into a low power consumption state to save power when the device enters this state. Note that the MachXO2 devices are powered on when in standby mode and all power supplies should remain in the Recommended Operating Conditions.

Table 2-18. MachXO2 Power Saving Features Description

Device Subsystem	Feature Description
Bandgap	The bandgap can be turned off in standby mode. When the Bandgap is turned off, analog circuitry such as the POR, PLLs, on-chip oscillator, and referenced and differential I/O buffers are also turned off. Bandgap can only be turned off for 1.2 V devices.
Power-On-Reset (POR)	The POR can be turned off in standby mode. This monitors VCC levels. In the event of unsafe V_{CC} drops, this circuit reconfigures the device. When the POR circuitry is turned off, limited power detector circuitry is still active. This option is only recommended for applications in which the power supply rails are reliable.
On-Chip Oscillator	The on-chip oscillator has two power saving features. It may be switched off if it is not needed in your design. It can also be turned off in Standby mode.
PLL	Similar to the on-chip oscillator, the PLL also has two power saving features. It can be statically switched off if it is not needed in a design. It can also be turned off in Standby mode. The PLL will wait until all output clocks from the PLL are driven low before powering off.
I/O Bank Controller	Referenced and differential I/O buffers (used to implement standards such as HSTL, SSTL and LVDS) consume more than ratioed single-ended I/Os such as LVCMOS and LVTTL. The I/O bank controller allows the user to turn these I/Os off dynamically on a per bank selection.
Dynamic Clock Enable for Primary Clock Nets	Each primary clock net can be dynamically disabled to save power.
Power Guard	Power Guard is a feature implemented in input buffers. This feature allows users to switch off the input buffer when it is not needed. This feature can be used in both clock and data paths. Its biggest impact is that in the standby mode it can be used to switch off clock inputs that are distributed using general routing resources.

For more details on the standby mode refer to TN1198, Power Estimation and Management for MachXO2 Devices.

Power On Reset

MachXO2 devices have power-on reset circuitry to monitor V_{CCINT} and V_{CCIO} voltage levels during power-up and operation. At power-up, the POR circuitry monitors V_{CCINT} and V_{CCIO0} (controls configuration) voltage levels. It then triggers download from the on-chip configuration Flash memory after reaching the V_{PORUP} level specified in the Power-On-Reset Voltage table in the DC and Switching Characteristics section of this data sheet. For devices without voltage regulators (ZE and HE devices), V_{CCINT} is the same as the V_{CC} supply voltage. For devices with voltage regulators (HC devices), V_{CCINT} is regulated from the V_{CC} supply voltage. From this voltage reference, the time taken for configuration and entry into user mode is specified as Flash Download Time ($t_{REFRESH}$) in the DC and Switching Characteristics section of this data sheet. Before and during configuration, the I/Os are held in tri-state. I/Os are released to user functionality once the device has finished configuration. Note that for HC devices, a separate POR circuit monitors external V_{CC} voltage in addition to the POR circuit that monitors the internal post-regulated power supply voltage level.

Once the device enters into user mode, the POR circuitry can optionally continue to monitor V_{CCINT} levels. If V_{CCINT} drops below $V_{PORDNBG}$ level (with the bandgap circuitry switched on) or below $V_{PORDNSRAM}$ level (with the bandgap circuitry switched off to conserve power) device functionality cannot be guaranteed. In such a situation the POR issues a reset and begins monitoring the V_{CCINT} and V_{CCIO} voltage levels. $V_{PORDNBG}$ and $V_{PORDNSRAM}$ are both specified in the Power-On-Reset Voltage table in the DC and Switching Characteristics section of this data sheet.

Note that once a ZE or HE device enters user mode, users can switch off the bandgap to conserve power. When the bandgap circuitry is switched off, the POR circuitry also shuts down. The device is designed such that a minimal, low power POR circuit is still operational (this corresponds to the $V_{PORDNSRAM}$ reset point described in the paragraph above). However this circuit is not as accurate as the one that operates when the bandgap is switched on. The low power POR circuit emulates an SRAM cell and is biased to trip before the vast majority of SRAM cells flip. If users are concerned about the V_{CC} supply dropping below V_{CC} (min) they should not shut down the bandgap or POR circuit.

Power-On-Reset Voltage Levels[1, 2, 3, 4, 5]

Symbol	Parameter	Min.	Typ.	Max.	Units
V_{PORUP}	Power-On-Reset ramp up trip point (band gap based circuit monitoring V_{CCINT} and V_{CCIO0})	0.9	—	1.06	V
$V_{PORUPEXT}$	Power-On-Reset ramp up trip point (band gap based circuit monitoring external V_{CC} power supply)	1.5	—	2.1	V
$V_{PORDNBG}$	Power-On-Reset ramp down trip point (band gap based circuit monitoring V_{CCINT})	0.75	—	0.93	V
$V_{PORDNBGEXT}$	Power-On-Reset ramp down trip point (band gap based circuit monitoring V_{CC})	0.98	—	1.33	V
$V_{PORDNSRAM}$	Power-On-Reset ramp down trip point (SRAM based circuit monitoring V_{CCINT})	—	0.6	—	V
$V_{PORDNSRAMEXT}$	Power-On-Reset ramp down trip point (SRAM based circuit monitoring V_{CC})	—	0.96	—	V

1. These POR trip points are only provided for guidance. Device operation is only characterized for power supply voltages specified under recommended operating conditions.
2. For devices without voltage regulators V_{CCINT} is the same as the V_{CC} supply voltage. For devices with voltage regulators, V_{CCINT} is regulated from the V_{CC} supply voltage.
3. Note that V_{PORUP} (min.) and $V_{PORDNBG}$ (max.) are in different process corners. For any given process corner $V_{PORDNBG}$ (max.) is always 12.0 mV below V_{PORUP} (min.).
4. $V_{PORUPEXT}$ is for HC devices only. In these devices a separate POR circuit monitors the external V_{CC} power supply.
5. V_{CCIO0} does not have a Power-On-Reset ramp down trip point. V_{CCIO0} must remain within the Recommended Operating Conditions to ensure proper operation.

Programming/Erase Specifications

Symbol	Parameter	Min.	Max.[1]	Units
$N_{PROGCYC}$	Flash Programming cycles per $t_{RETENTION}$	—	10,000	Cycles
	Flash functional programming cycles	—	100,000	
$t_{RETENTION}$	Data retention at 100 °C junction temperature	10	—	Years
	Data retention at 85 °C junction temperature	20	—	

1. Maximum Flash memory reads are limited to 7.5E13 cycles over the lifetime of the product.

Hot Socketing Specifications[1, 2, 3]

Symbol	Parameter	Condition	Max.	Units
I_{DK}	Input or I/O leakage Current	$0 < V_{IN} < V_{IH}$ (MAX)	+/–1000	µA

1. Insensitive to sequence of V_{CC} and V_{CCIO}. However, assumes monotonic rise/fall rates for V_{CC} and V_{CCIO}.
2. $0 < V_{CC} < V_{CC}$ (MAX), $0 < V_{CCIO} < V_{CCIO}$ (MAX).
3. I_{DK} is additive to I_{PU}, I_{PD} or I_{BH}.

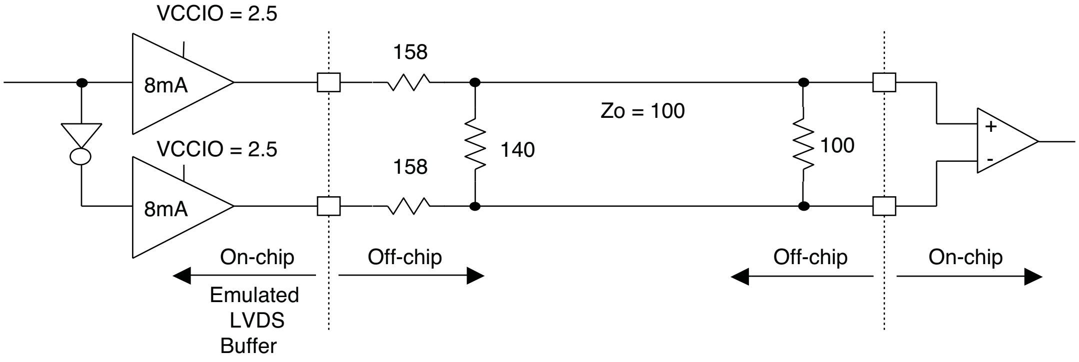
ESD Performance

Please refer to the MachXO2 Product Family Qualification Summary for complete qualification data, including ESD performance.

LVDS Emulation

MachXO2 devices can support LVDS outputs via emulation (LVDS25E). The output is emulated using complementary LVCMOS outputs in conjunction with resistors across the driver outputs on all devices. The scheme shown in Figure 3-1 is one possible solution for LVDS standard implementation. Resistor values in Figure 3-1 are industry standard values for 1% resistors.

Figure 3-1. LVDS Using External Resistors (LVDS25E)



Note: All resistors are ±1%.

Table 3-1. LVDS25E DC Conditions

Over Recommended Operating Conditions

Parameter	Description	Typ.	Units
Z_{OUT}	Output impedance	20	Ohms
R_S	Driver series resistor	158	Ohms
R_P	Driver parallel resistor	140	Ohms
R_T	Receiver termination	100	Ohms
V_{OH}	Output high voltage	1.43	V
V_{OL}	Output low voltage	1.07	V
V_{OD}	Output differential voltage	0.35	V
V_{CM}	Output common mode voltage	1.25	V
Z_{BACK}	Back impedance	100.5	Ohms
I_{DC}	DC output current	6.03	mA

LVPECL

The MachXO2 family supports the differential LVPECL standard through emulation. This output standard is emulated using complementary LVCMOS outputs in conjunction with resistors across the driver outputs on all the devices. The LVPECL input standard is supported by the LVDS differential input buffer. The scheme shown in Differential LVPECL is one possible solution for point-to-point signals.

Figure 3-3. Differential LVPECL

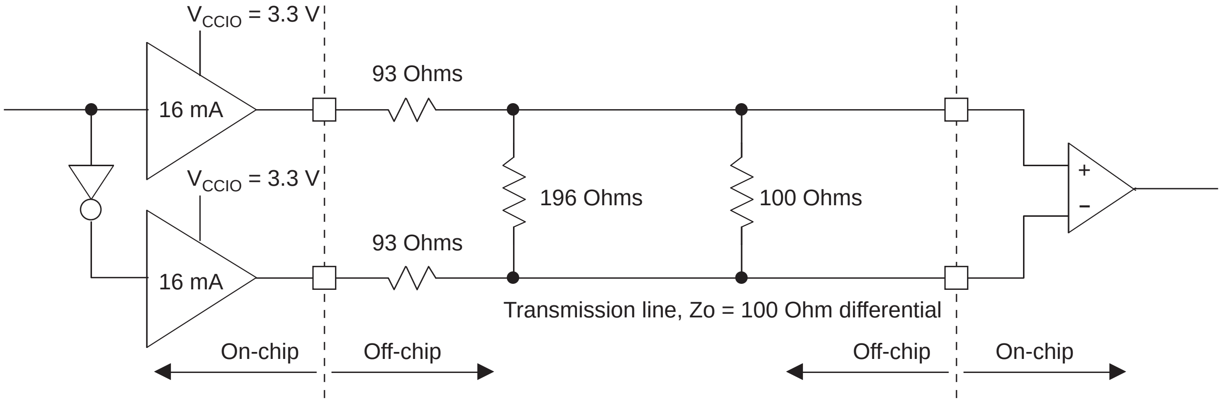


Table 3-3. LVPECL DC Conditions[1]

Over Recommended Operating Conditions

Symbol	Description	Nominal	Units
Z_{OUT}	Output impedance	20	Ohms
R_S	Driver series resistor	93	Ohms
R_P	Driver parallel resistor	196	Ohms
R_T	Receiver termination	100	Ohms
V_{OH}	Output high voltage	2.05	V
V_{OL}	Output low voltage	1.25	V
V_{OD}	Output differential voltage	0.80	V
V_{CM}	Output common mode voltage	1.65	V
Z_{BACK}	Back impedance	100.5	Ohms
I_{DC}	DC output current	12.11	mA

1. For input buffer, see LVDS table.

For further information on LVPECL, BLVDS and other differential interfaces please see details of additional technical documentation at the end of the data sheet.

Typical Building Block Function Performance – HC/HE Devices[1]

Pin-to-Pin Performance (LVCMOS25 12 mA Drive)

Function	-6 Timing	Units
Basic Functions		
16-bit decoder	8.9	ns
4:1 MUX	7.5	ns
16:1 MUX	8.3	ns

Register-to-Register Performance

Function	-6 Timing	Units
Basic Functions		
16:1 MUX	412	MHz
16-bit adder	297	MHz
16-bit counter	324	MHz
64-bit counter	161	MHz
Embedded Memory Functions		
1024x9 True-Dual Port RAM (Write Through or Normal, EBR output registers)	183	MHz
Distributed Memory Functions		
16x4 Pseudo-Dual Port RAM (one PFU)	500	MHz

1. The above timing numbers are generated using the Diamond design tool. Exact performance may vary with device and tool version. The tool uses internal parameters that have been characterized but are not tested on every device. Commercial timing numbers are shown at 85 °C and 1.14 V. Other operating conditions, including industrial, can be extracted from the Diamond software.

Maximum sysIO Buffer Performance

I/O Standard	Max. Speed	Units
LVDS25	400	MHz
LVDS25E	150	MHz
RSDS25	150	MHz
RSDS25E	150	MHz
BLVDS25	150	MHz
BLVDS25E	150	MHz
MLVDS25	150	MHz
MLVDS25E	150	MHz
LVPECL33	150	MHz
LVPECL33E	150	MHz
SSTL25_I	150	MHz
SSTL25_II	150	MHz
SSTL25D_I	150	MHz
SSTL25D_II	150	MHz
SSTL18_I	150	MHz
SSTL18_II	150	MHz
SSTL18D_I	150	MHz
SSTL18D_II	150	MHz
HSTL18_I	150	MHz
HSTL18_II	150	MHz
HSTL18D_I	150	MHz
HSTL18D_II	150	MHz
PCI33	134	MHz
LVTTL33	150	MHz
LVTTL33D	150	MHz
LVCMOS33	150	MHz
LVCMOS33D	150	MHz
LVCMOS25	150	MHz
LVCMOS25D	150	MHz
LVCMOS25R33	150	MHz
LVCMOS18	150	MHz
LVCMOS18D	150	MHz
LVCMOS18R33	150	MHz
LVCMOS18R25	150	MHz
LVCMOS15	150	MHz
LVCMOS15D	150	MHz
LVCMOS15R33	150	MHz
LVCMOS15R25	150	MHz
LVCMOS12	91	MHz
LVCMOS12D	91	MHz

Parameter	Description	Device	–6		–5		–4		Units
			Min.	Max.	Min.	Max.	Min.	Max.	
LPDDR[9, 12]									
t_{DVADQ}	Input Data Valid After DQS Input	MachXO2-1200/U and larger devices, right side only.[13]	—	0.369	—	0.395	—	0.421	UI
t_{DVEDQ}	Input Data Hold After DQS Input		0.529	—	0.530	—	0.527	—	UI
t_{DQVBS}	Output Data Invalid Before DQS Output		0.25	—	0.25	—	0.25	—	UI
t_{DQVAS}	Output Data Invalid After DQS Output		0.25	—	0.25	—	0.25	—	UI
f_{DATA}	MEM LPDDR Serial Data Speed		—	280	—	250	—	208	Mbps
f_{SCLK}	SCLK Frequency		—	140	—	125	—	104	MHz
f_{LPDDR}	LPDDR Data Transfer Rate		0	280	0	250	0	208	Mbps
DDR[9, 12]									
t_{DVADQ}	Input Data Valid After DQS Input	MachXO2-1200/U and larger devices, right side only.[13]	—	0.350	—	0.387	—	0.414	UI
t_{DVEDQ}	Input Data Hold After DQS Input		0.545	—	0.538	—	0.532	—	UI
t_{DQVBS}	Output Data Invalid Before DQS Output		0.25	—	0.25	—	0.25	—	UI
t_{DQVAS}	Output Data Invalid After DQS Output		0.25	—	0.25	—	0.25	—	UI
f_{DATA}	MEM DDR Serial Data Speed		—	300	—	250	—	208	Mbps
f_{SCLK}	SCLK Frequency		—	150	—	125	—	104	MHz
f_{MEM_DDR}	MEM DDR Data Transfer Rate		N/A	300	N/A	250	N/A	208	Mbps
DDR2[9, 12]									
t_{DVADQ}	Input Data Valid After DQS Input	MachXO2-1200/U and larger devices, right side only.[13]	—	0.360	—	0.378	—	0.406	UI
t_{DVEDQ}	Input Data Hold After DQS Input		0.555	—	0.549	—	0.542	—	UI
t_{DQVBS}	Output Data Invalid Before DQS Output		0.25	—	0.25	—	0.25	—	UI
t_{DQVAS}	Output Data Invalid After DQS Output		0.25	—	0.25	—	0.25	—	UI
f_{DATA}	MEM DDR Serial Data Speed		—	300	—	250	—	208	Mbps
f_{SCLK}	SCLK Frequency		—	150	—	125	—	104	MHz
f_{MEM_DDR2}	MEM DDR2 Data Transfer Rate		N/A	300	N/A	250	N/A	208	Mbps

1. Exact performance may vary with device and design implementation. Commercial timing numbers are shown at 85 °C and 1.14 V. Other operating conditions, including industrial, can be extracted from the Diamond software.
2. General I/O timing numbers based on LVCMOS 2.5, 8 mA, 0pf load, fast slew rate.
3. Generic DDR timing numbers based on LVDS I/O (for input, output, and clock ports).
4. DDR timing numbers based on SSTL25. DDR2 timing numbers based on SSTL18. LPDDR timing numbers based in LVCMOS18.
5. 7:1 LVDS (GDDR71) uses the LVDS I/O standard (for input, output, and clock ports).
6. For Generic DDRX1 mode $t_{SU} = t_{HO} = (t_{DVE} - t_{DVA} - 0.03\text{ ns})/2$.
7. The t_{SU_DEL} and t_{H_DEL} values use the SCLK_ZERHOLD default step size. Each step is 105 ps (–6), 113 ps (–5), 120 ps (–4).
8. This number for general purpose usage. Duty cycle tolerance is +/– 10%.
9. Duty cycle is +/–5% for system usage.
10. The above timing numbers are generated using the Diamond design tool. Exact performance may vary with the device selected.
11. High-speed DDR and LVDS not supported in SG32 (32 QFN) packages.
12. Advance information for MachXO2 devices in 48 QFN packages.
13. DDR memory interface not supported in QN84 (84 QFN) and SG32 (32 QFN) packages.

Parameter	Description	Device	–3		–2		–1		Units
			Min.	Max.	Min.	Max.	Min.	Max.	
Generic DDR4 Inputs with Clock and Data Centered at Pin Using PCLK Pin for Clock Input – GDDRX4_RX.ECLK.Centered[9, 12]									
t_{SU}	Input Data Setup Before ECLK	MachXO2-640U, MachXO2-1200/U and larger devices, bottom side only[11]	0.434	—	0.535	—	0.630	—	ns
t_{HO}	Input Data Hold After ECLK		0.385	—	0.395	—	0.463	—	ns
f_{DATA}	DDRX4 Serial Input Data Speed		—	420	—	352	—	292	Mbps
f_{DDRX4}	DDRX4 ECLK Frequency		—	210	—	176	—	146	MHz
f_{SCLK}	SCLK Frequency		—	53	—	44	—	37	MHz
7:1 LVDS Inputs – GDDR71_RX.ECLK.7.1[9, 12]									
t_{DVA}	Input Data Valid After ECLK	MachXO2-640U, MachXO2-1200/U and larger devices, bottom side only[11]	—	0.307	—	0.316	—	0.326	UI
t_{DVE}	Input Data Hold After ECLK		0.662	—	0.650	—	0.649	—	UI
f_{DATA}	DDR71 Serial Input Data Speed		—	420	—	352	—	292	Mbps
f_{DDR71}	DDR71 ECLK Frequency		—	210	—	176	—	146	MHz
f_{CLKIN}	7:1 Input Clock Frequency (SCLK) (minimum limited by PLL)		—	60	—	50	—	42	MHz
Generic DDR Outputs with Clock and Data Aligned at Pin Using PCLK Pin for Clock Input – GDDRX1_TX.SCLK.Aligned[9, 12]									
t_{DIA}	Output Data Invalid After CLK Output	All MachXO2 devices, all sides	—	0.850	—	0.910	—	0.970	ns
t_{DIB}	Output Data Invalid Before CLK Output		—	0.850	—	0.910	—	0.970	ns
f_{DATA}	DDRX1 Output Data Speed		—	140	—	116	—	98	Mbps
f_{DDRX1}	DDRX1 SCLK frequency		—	70	—	58	—	49	MHz
Generic DDR Outputs with Clock and Data Centered at Pin Using PCLK Pin for Clock Input – GDDRX1_TX.SCLK.Centered[9, 12]									
t_{DVB}	Output Data Valid Before CLK Output	All MachXO2 devices, all sides	2.720	—	3.380	—	4.140	—	ns
t_{DVA}	Output Data Valid After CLK Output		2.720	—	3.380	—	4.140	—	ns
f_{DATA}	DDRX1 Output Data Speed		—	140	—	116	—	98	Mbps
f_{DDRX1}	DDRX1 SCLK Frequency (minimum limited by PLL)		—	70	—	58	—	49	MHz
Generic DDRX2 Outputs with Clock and Data Aligned at Pin Using PCLK Pin for Clock Input – GDDRX2_TX.ECLK.Aligned[9, 12]									
t_{DIA}	Output Data Invalid After CLK Output	MachXO2-640U, MachXO2-1200/U and larger devices, top side only	—	0.270	—	0.300	—	0.330	ns
t_{DIB}	Output Data Invalid Before CLK Output		—	0.270	—	0.300	—	0.330	ns
f_{DATA}	DDRX2 Serial Output Data Speed		—	280	—	234	—	194	Mbps
f_{DDRX2}	DDRX2 ECLK frequency		—	140	—	117	—	97	MHz
f_{SCLK}	SCLK Frequency		—	70	—	59	—	49	MHz

Parameter	Description	Device	–3		–2		–1		Units
			Min.	Max.	Min.	Max.	Min.	Max.	
Generic DDRX2 Outputs with Clock and Data Centered at Pin Using PCLK Pin for Clock Input – GDDRX2_TX.ECLK.Centered[9, 12]									
t_{DVB}	Output Data Valid Before CLK Output	MachXO2-640U, MachXO2-1200/U and larger devices, top side only	1.445	—	1.760	—	2.140	—	ns
t_{DVA}	Output Data Valid After CLK Output		1.445	—	1.760	—	2.140	—	ns
f_{DATA}	DDRX2 Serial Output Data Speed		—	280	—	234	—	194	Mbps
f_{DDRX2}	DDRX2 ECLK Frequency (minimum limited by PLL)		—	140	—	117	—	97	MHz
f_{SCLK}	SCLK Frequency		—	70	—	59	—	49	MHz
Generic DDRX4 Outputs with Clock and Data Aligned at Pin Using PCLK Pin for Clock Input – GDDRX4_TX.ECLK.Aligned[9, 12]									
t_{DIA}	Output Data Invalid After CLK Output	MachXO2-640U, MachXO2-1200/U and larger devices, top side only	—	0.270	—	0.300	—	0.330	ns
t_{DIB}	Output Data Invalid Before CLK Output		—	0.270	—	0.300	—	0.330	ns
f_{DATA}	DDRX4 Serial Output Data Speed		—	420	—	352	—	292	Mbps
f_{DDRX4}	DDRX4 ECLK Frequency		—	210	—	176	—	146	MHz
f_{SCLK}	SCLK Frequency		—	53	—	44	—	37	MHz
Generic DDRX4 Outputs with Clock and Data Centered at Pin Using PCLK Pin for Clock Input – GDDRX4_TX.ECLK.Centered[9, 12]									
t_{DVB}	Output Data Valid Before CLK Output	MachXO2-640U, MachXO2-1200/U and larger devices, top side only	0.873	—	1.067	—	1.319	—	ns
t_{DVA}	Output Data Valid After CLK Output		0.873	—	1.067	—	1.319	—	ns
f_{DATA}	DDRX4 Serial Output Data Speed		—	420	—	352	—	292	Mbps
f_{DDRX4}	DDRX4 ECLK Frequency (minimum limited by PLL)		—	210	—	176	—	146	MHz
f_{SCLK}	SCLK Frequency		—	53	—	44	—	37	MHz
7:1 LVDS Outputs – GDDR71_TX.ECLK.7:1[9, 12]									
t_{DIB}	Output Data Invalid Before CLK Output	MachXO2-640U, MachXO2-1200/U and larger devices, top side only.	—	0.240	—	0.270	—	0.300	ns
t_{DIA}	Output Data Invalid After CLK Output		—	0.240	—	0.270	—	0.300	ns
f_{DATA}	DDR71 Serial Output Data Speed		—	420	—	352	—	292	Mbps
f_{DDR71}	DDR71 ECLK Frequency		—	210	—	176	—	146	MHz
f_{CLKOUT}	7:1 Output Clock Frequency (SCLK) (minimum limited by PLL)		—	60	—	50	—	42	MHz

sysCLOCK PLL Timing

Over Recommended Operating Conditions

Parameter	Descriptions	Conditions	Min.	Max.	Units
f_{IN}	Input Clock Frequency (CLKI, CLKFB)		7	400	MHz
f_{OUT}	Output Clock Frequency (CLKOP, CLKOS, CLKOS2)		1.5625	400	MHz
f_{OUT2}	Output Frequency (CLKOS3 cascaded from CLKOS2)		0.0122	400	MHz
f_{VCO}	PLL VCO Frequency		200	800	MHz
f_{PFD}	Phase Detector Input Frequency		7	400	MHz
AC Characteristics					
t_{DT}	Output Clock Duty Cycle	Without duty trim selected[3]	45	55	%
t_{DT_TRIM}[7]	Edge Duty Trim Accuracy		–75	75	%
t_{PH}[4]	Output Phase Accuracy		–6	6	%
t_{OPJIT}[1, 8]	Output Clock Period Jitter	$f_{OUT} > 100$ MHz	—	150	ps p-p
		$f_{OUT} < 100$ MHz	—	0.007	UIPP
	Output Clock Cycle-to-cycle Jitter	$f_{OUT} > 100$ MHz	—	180	ps p-p
		$f_{OUT} < 100$ MHz	—	0.009	UIPP
	Output Clock Phase Jitter	$f_{PFD} > 100$ MHz	—	160	ps p-p
		$f_{PFD} < 100$ MHz	—	0.011	UIPP
	Output Clock Period Jitter (Fractional-N)	$f_{OUT} > 100$ MHz	—	230	ps p-p
		$f_{OUT} < 100$ MHz	—	0.12	UIPP
	Output Clock Cycle-to-cycle Jitter (Fractional-N)	$f_{OUT} > 100$ MHz	—	230	ps p-p
		$f_{OUT} < 100$ MHz	—	0.12	UIPP
t_{SPO}	Static Phase Offset	Divider ratio = integer	–120	120	ps
t_{W}	Output Clock Pulse Width	At 90% or 10%[3]	0.9	—	ns
t_{LOCK}[2, 5]	PLL Lock-in Time		—	15	ms
t_{UNLOCK}	PLL Unlock Time		—	50	ns
t_{IPJIT}[6]	Input Clock Period Jitter	$f_{PFD} \geq 20$ MHz	—	1,000	ps p-p
		$f_{PFD} < 20$ MHz	—	0.02	UIPP
t_{HI}	Input Clock High Time	90% to 90%	0.5	—	ns
t_{LO}	Input Clock Low Time	10% to 10%	0.5	—	ns
t_{STABLE}[5]	STANDBY High to PLL Stable		—	15	ms
t_{RST}	RST/RESETM Pulse Width		1	—	ns
t_{RSTREC}	RST Recovery Time		1	—	ns
t_{RST_DIV}	RESETC/D Pulse Width		10	—	ns
t_{RSTREC_DIV}	RESETC/D Recovery Time		1	—	ns
$t_{ROTATE\text{-}SETUP}$	PHASESTEP Setup Time		10	—	ns

For Further Information

For further information regarding logic signal connections for various packages please refer to the MachXO2 Device Pinout Files.

Thermal Management

Thermal management is recommended as part of any sound FPGA design methodology. To assess the thermal characteristics of a system, Lattice specifies a maximum allowable junction temperature in all device data sheets. Users must complete a thermal analysis of their specific design to ensure that the device and package do not exceed the junction temperature limits. Refer to the Thermal Management document to find the device/package specific thermal values.

For Further Information

For further information regarding Thermal Management, refer to the following:

- Thermal Management document
- TN1198, Power Estimation and Management for MachXO2 Devices
- The Power Calculator tool is included with the Lattice design tools, or as a standalone download from www.latticesemi.com/software

Ultra Low Power Commercial Grade Devices, Halogen Free (RoHS) Packaging

Part Number	LUTs	Supply Voltage	Grade	Package	Leads	Temp.
LCMXO2-256ZE-1SG32C	256	1.2 V	–1	Halogen-Free QFN	32	COM
LCMXO2-256ZE-2SG32C	256	1.2 V	–2	Halogen-Free QFN	32	COM
LCMXO2-256ZE-3SG32C	256	1.2 V	–3	Halogen-Free QFN	32	COM
LCMXO2-256ZE-1UMG64C	256	1.2 V	–1	Halogen-Free ucBGA	64	COM
LCMXO2-256ZE-2UMG64C	256	1.2 V	–2	Halogen-Free ucBGA	64	COM
LCMXO2-256ZE-3UMG64C	256	1.2 V	–3	Halogen-Free ucBGA	64	COM
LCMXO2-256ZE-1TG100C	256	1.2 V	–1	Halogen-Free TQFP	100	COM
LCMXO2-256ZE-2TG100C	256	1.2 V	–2	Halogen-Free TQFP	100	COM
LCMXO2-256ZE-3TG100C	256	1.2 V	–3	Halogen-Free TQFP	100	COM
LCMXO2-256ZE-1MG132C	256	1.2 V	–1	Halogen-Free csBGA	132	COM
LCMXO2-256ZE-2MG132C	256	1.2 V	–2	Halogen-Free csBGA	132	COM
LCMXO2-256ZE-3MG132C	256	1.2 V	–3	Halogen-Free csBGA	132	COM

Part Number	LUTs	Supply Voltage	Grade	Package	Leads	Temp.
LCMXO2-640ZE-1TG100C	640	1.2 V	–1	Halogen-Free TQFP	100	COM
LCMXO2-640ZE-2TG100C	640	1.2 V	–2	Halogen-Free TQFP	100	COM
LCMXO2-640ZE-3TG100C	640	1.2 V	–3	Halogen-Free TQFP	100	COM
LCMXO2-640ZE-1MG132C	640	1.2 V	–1	Halogen-Free csBGA	132	COM
LCMXO2-640ZE-2MG132C	640	1.2 V	–2	Halogen-Free csBGA	132	COM
LCMXO2-640ZE-3MG132C	640	1.2 V	–3	Halogen-Free csBGA	132	COM

Part Number	LUTs	Supply Voltage	Grade	Package	Leads	Temp.
LCMXO2-1200ZE-1SG32C	1280	1.2 V	–1	Halogen-Free QFN	32	COM
LCMXO2-1200ZE-2SG32C	1280	1.2 V	–2	Halogen-Free QFN	32	COM
LCMXO2-1200ZE-3SG32C	1280	1.2 V	–3	Halogen-Free QFN	32	COM
LCMXO2-1200ZE-1TG100C	1280	1.2 V	–1	Halogen-Free TQFP	100	COM
LCMXO2-1200ZE-2TG100C	1280	1.2 V	–2	Halogen-Free TQFP	100	COM
LCMXO2-1200ZE-3TG100C	1280	1.2 V	–3	Halogen-Free TQFP	100	COM
LCMXO2-1200ZE-1MG132C	1280	1.2 V	–1	Halogen-Free csBGA	132	COM
LCMXO2-1200ZE-2MG132C	1280	1.2 V	–2	Halogen-Free csBGA	132	COM
LCMXO2-1200ZE-3MG132C	1280	1.2 V	–3	Halogen-Free csBGA	132	COM
LCMXO2-1200ZE-1TG144C	1280	1.2 V	–1	Halogen-Free TQFP	144	COM
LCMXO2-1200ZE-2TG144C	1280	1.2 V	–2	Halogen-Free TQFP	144	COM
LCMXO2-1200ZE-3TG144C	1280	1.2 V	–3	Halogen-Free TQFP	144	COM

Part Number	LUTs	Supply Voltage	Grade	Package	Leads	Temp.
LCMXO2-2000UHC-4FG484C	2112	2.5 V / 3.3 V	–4	Halogen-Free fpBGA	484	COM
LCMXO2-2000UHC-5FG484C	2112	2.5 V / 3.3 V	–5	Halogen-Free fpBGA	484	COM
LCMXO2-2000UHC-6FG484C	2112	2.5 V / 3.3 V	–6	Halogen-Free fpBGA	484	COM

Part Number	LUTs	Supply Voltage	Grade	Package	Leads	Temp.
LCMXO2-4000HC-4QN84C	4320	2.5 V / 3.3 V	–4	Halogen-Free QFN	84	COM
LCMXO2-4000HC-5QN84C	4320	2.5 V / 3.3 V	–5	Halogen-Free QFN	84	COM
LCMXO2-4000HC-6QN84C	4320	2.5 V / 3.3 V	–6	Halogen-Free QFN	84	COM
LCMXO2-4000HC-4MG132C	4320	2.5 V / 3.3 V	–4	Halogen-Free csBGA	132	COM
LCMXO2-4000HC-5MG132C	4320	2.5 V / 3.3 V	–5	Halogen-Free csBGA	132	COM
LCMXO2-4000HC-6MG132C	4320	2.5 V / 3.3 V	–6	Halogen-Free csBGA	132	COM
LCMXO2-4000HC-4TG144C	4320	2.5 V / 3.3 V	–4	Halogen-Free TQFP	144	COM
LCMXO2-4000HC-5TG144C	4320	2.5 V / 3.3 V	–5	Halogen-Free TQFP	144	COM
LCMXO2-4000HC-6TG144C	4320	2.5 V / 3.3 V	–6	Halogen-Free TQFP	144	COM
LCMXO2-4000HC-4BG256C	4320	2.5 V / 3.3 V	–4	Halogen-Free caBGA	256	COM
LCMXO2-4000HC-5BG256C	4320	2.5 V / 3.3 V	–5	Halogen-Free caBGA	256	COM
LCMXO2-4000HC-6BG256C	4320	2.5 V / 3.3 V	–6	Halogen-Free caBGA	256	COM
LCMXO2-4000HC-4FTG256C	4320	2.5 V / 3.3 V	–4	Halogen-Free ftBGA	256	COM
LCMXO2-4000HC-5FTG256C	4320	2.5 V / 3.3 V	–5	Halogen-Free ftBGA	256	COM
LCMXO2-4000HC-6FTG256C	4320	2.5 V / 3.3 V	–6	Halogen-Free ftBGA	256	COM
LCMXO2-4000HC-4BG332C	4320	2.5 V / 3.3 V	–4	Halogen-Free caBGA	332	COM
LCMXO2-4000HC-5BG332C	4320	2.5 V / 3.3 V	–5	Halogen-Free caBGA	332	COM
LCMXO2-4000HC-6BG332C	4320	2.5 V / 3.3 V	–6	Halogen-Free caBGA	332	COM
LCMXO2-4000HC-4FG484C	4320	2.5 V / 3.3 V	–4	Halogen-Free fpBGA	484	COM
LCMXO2-4000HC-5FG484C	4320	2.5 V / 3.3 V	–5	Halogen-Free fpBGA	484	COM
LCMXO2-4000HC-6FG484C	4320	2.5 V / 3.3 V	–6	Halogen-Free fpBGA	484	COM

R1 Device Specifications

The LCMXO2-1200ZE/HC "R1" devices have the same specifications as their Standard (non-R1) counterparts except as listed below. For more details on the R1 to Standard migration refer to AN8086, Designing for Migration from MachXO2-1200-R1 to Standard Non-R1) Devices.

- The User Flash Memory (UFM) cannot be programmed through the internal WISHBONE interface. It can still be programmed through the JTAG/SPI/I^{2}C ports.
- The on-chip differential input termination resistor value is higher than intended. It is approximately 200Ω as opposed to the intended 100Ω. It is recommended to use external termination resistors for differential inputs. The on-chip termination resistors can be disabled through Lattice design software.
- Soft Error Detection logic may not produce the correct result when it is run for the first time after configuration. To use this feature, discard the result from the first operation. Subsequent operations will produce the correct result.
- Under certain conditions, IIH exceeds data sheet specifications. The following table provides more details:

Condition	Clamp	Pad Rising IIH Max.	Pad Falling IIH Min.	Steady State Pad High IIH	Steady State Pad Low IIL
VPAD > VCCIO	OFF	1 mA	–1 mA	1 mA	10 µA
VPAD = VCCIO	ON	10 µA	–10 µA	10 µA	10 µA
VPAD = VCCIO	OFF	1 mA	–1 mA	1 mA	10 µA
VPAD < VCCIO	OFF	10 µA	–10 µA	10 µA	10 µA

- The user SPI interface does not operate correctly in some situations. During master read access and slave write access, the last byte received does not generate the RRDY interrupt.
- In GDDRX2, GDDRX4 and GDDR71 modes, ECLKSYNC may have a glitch in the output under certain conditions, leading to possible loss of synchronization.
- When using the hard I^{2}C IP core, the I^{2}C status registers I2C_1_SR and I2C_2_SR may not update correctly.
- PLL Lock signal will glitch high when coming out of standby. This glitch lasts for about 10 µsec before returning low.
- Dual boot only available on HC devices, requires tying VCC and VCCIO2 to the same 3.3 V or 2.5 V supply.